ERRATUM

Erratum: "Silicon oxidation and Si–SiO_2 interface of thin oxides" [J. Mater. Res. 2, 216 (1987)]

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After this article was published in the March/April issue of *Journal of Materials Research*, two errors were brought to our attention by its authors. First, the present affiliation footnote should be attributed to N. M. Ravindra. Second, the next to the last sentence of the abstract contains an incorrect unit of measure. The phrase "...silicon atoms of 1 mm size..." should be "...silicon atoms of 1 nm size... ." The corrected sentence should read: "Attempts aimed at correlating the high-resolution transmission electron micrographs with some physical parameters like the refractive index and the dielectric breakdown lead to considerations of the importance of the effect of protrusions of silicon atoms of 1 nm size into SiO_2 layers on the interface properties."

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